NEW NIST PUBLICATION
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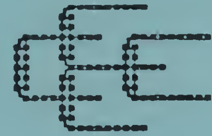
Center for Electronics and Electrical Engineering



Technical Progress Bulletin

Covering Center Programs, April to June 1989, with 1989 CEEE Events Calendar

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INTRODUCTION TO OCTOBER 1989 ISSUE OF THE CEEE TECHNICAL PROGRESS BULLETIN

This is the twenty-seventh issue of a quarterly publication providing information on the technical work of the National Institute of Standards and Technology (formerly the National Bureau of Standards) Center for Electronics and Electrical Engineering. This issue of the CEEE Technical Progress Bulletin covers the second quarter of calendar year 1989.

Organization of Bulletin: This issue contains abstracts for all Center papers released for publication by NIST in the quarter and citations and abstracts for Center papers published in the quarter. Entries are arranged by technical topic as identified in the table of contents and alphabetically by first author under each subheading within each topic. Unpublished papers appear under the subheading "Released for Publication". Papers published in the quarter appear under the subheading "Recently Published". Following each abstract is the name and telephone number of the individual to contact for more information on the topic (usually the first author). This issue also includes a calendar of Center conferences and workshops planned for calendar year 1989 and and 1990 and a list of sponsors of the work.

Center for Electronics and Electrical Engineering: Center programs provide national reference standards, measurement methods, supporting theory and data, and traceability to national standards.

The metrological products of these programs aid economic growth by promoting equity and efficiency in the marketplace, by removing metrological barriers to improved productivity and innovation, by increasing U. S. competitiveness in international markets through facilitation of compliance with international agreements, and by providing technical bases for the development of voluntary standards for domestic and international trade. These metrological products also aid in the development of rational regulatory policy and promote efficient functioning of technical programs of the Government.

The work of the Center is divided into two major programs: the Semiconductor Technology Program, carried out by the Semiconductor Electronics Division in Gaithersburg, MD, and the Signals and Systems Metrology Program, carried out by the Electrosystems Division in Gaithersburg and the Electromagnetic Fields and Electromagnetic Technology Divisions in Boulder, CO. Key contacts in the Center are given on the back cover; readers are encouraged to contact any of these individuals for further information. To request a subscription or for more information on the Bulletin, write to CEEE Technical Progress Bulletin, National Institute of Standards and Technology, Metrology Building, Room B-358, Gaithersburg, MD 20899 or call (301) 975-2220.

Center sponsors: The Center Programs are sponsored by the National Institute of Standards and Technology and a number of other organizations, in both the Federal and private sectors; these are identified on page 28.

Note on Publication Lists: Guides to earlier as well as recent work are the publication lists covering the work of each division. These lists are revised and reissued on an approximately annual basis and are available from the originating division. The current set is identified in the Additional Information section, page 26.

TABLE OF CONTENTS

INTRODUCTION . . . . inside front cover

SEMICONDUCTOR TECHNOLOGY PROGRAM 2

Silicon Materials 2
Dimensional Metrology 2
Analysis Techniques 4
Photodetectors 5
Power Devices 6
Integrated Circuit Test Structures 6
Device Physics and Modeling 7
Insulators and Interfaces 8
Other Semiconductor Metrology Topics 9

SIGNALS & SYSTEMS METROLOGY PROGRAM 10

FAST SIGNAL ACQUISITION, PROCESSING, & TRANSMISSION 10

Waveform Metrology 10
Cryoelectronic Metrology 11
Electro-Optic Metrology 13
DC & Low Frequency Metrology 15
Fundamental Electrical Measurements 15

ELECTRICAL SYSTEMS 18

Power Systems Metrology 18
Superconductors 20
Magnetic Materials & Measurements 25
Other Electrical Systems Topics 25

ELECTROMAGNETIC INTERFERENCE 25

Conducted Electromagnetic Interference 25

ADDITIONAL INFORMATION 26

1989/1990 CEEE CALENDAR 27

SPONSOR LIST 28

KEY CONTACTS IN CENTER, CENTER ORGANIZATION . . . . back cover

SEMICONDUCTOR TECHNOLOGY PROGRAM

Silicon Materials

Released for Publication

Mayo, S., Fassett, J.D., Kingston, H.M., and Walker, R.J., **Measurement of Vanadium Impurity in SIMOX Material by Isotope Dilution and Resonance Ionization Mass Spectrometry**.

The combined analytical capabilities of isotope dilution, laser-induced resonance ionization spectroscopy, and mass spectrometry, integrated in the resonance ionization mass spectrometry technique (RIMS), have been evaluated as a tool for quantitative elemental impurity analysis of SIMOX, a new silicon-based material prepared by oxygen implants. The vanadium impurity content was measured in the top crystalline SIMOX film and the oxygen-synthesized buried oxide layer in commercial wafers, resulting in 0.1 μg/g ± 20 percent, or 1.7 x 10^{15} atoms/cm^3. A similar analysis on the substrate bulk shows about 30 times lower vanadium impurity levels. The origin of this contamination is linked to the oxygen implant, although no modeling for it is offered here. The sensitivity of RIMS to vanadium is in the range of picograms per gram. The accuracy of results is determined by the blank, in view of the low total vanadium in the specimen.
[Contact: Santos Mayo, (301) 975-2045]

Recently Published

Kopanski, J.J., Albers, J., and Carver, G.P., **Experimental Verification of the Relation Between Two-Probe and Four-Probe Resistances**, Extended Abstract, Electrochemical Society Meeting, Los Angeles, California, May 7-12, 1989, pp. 367-368.

Recent innovations in the measurement of two-probe (spreading resistance) and four-probe resistance using an array of lithographically fabricated, geometrically well-defined contacts have enabled the measurement of these quantities with high accuracy and reproducibility. This has permitted experimental verification of the relationship between the two-probe resistances and the four-probe resistance. Verification was also made of the predicted dependence of the four-probe resistance on the ratio of wafer thickness to probe spacing for in-line and square probe configurations.
[Contact: Joseph J. Kopanski, (301) 975-2089]

Thurber, W.R., Lowney, J.R., Larrabee, R.D., Talwar, P., and Ehrstein, J.R., **An ac Impedance Method for High Resistivity Measurements of Silicon**, Extended Abstract, Electrochemical Society Meeting, Los Angeles, California, May 7-12, 1989, pp. 365-366.

An ac impedance method for measuring the average bulk resistivity of ingots and slices of high-resistivity silicon is described. Easily removable contacts, such as silver paste, are applied to the end faces of the sample and the impedance of the resulting capacitive sandwich is measured as a function of frequency. The resistivity can be calculated from the frequency of the negative peak in the imaginary part of the impedance and model consistency can be checked by comparison of values of resistance obtained from real and imaginary parts at this peak. Comparisons with van der Pauw and four-probe measurements are consistent with this impedance method.
[Contact: W. Robert Thurber, (301) 975-2057]

Dimensional Metrology

Released for Publication

Potzick, J.E., **Automated Calibration of Optical Photomask Linewidth Standards at the National Institute of Standards and Technology**.

An automated system has been developed

Dimensional Metrology (cont'd.)

at the National Institute of Standards and Technology for calibrating optical photomask linewidth standards. This system, controlled by a desktop computer, locates each feature to be measured in the field of view of the microscope, centers and focuses the image, scans the image, and calculates the optical linewidth from the scan data. The results are checked for errors and the process repeated until every feature of the photomask has been calibrated. If statistical tests are passed, a calibration certificate is printed.
[Contact: Beverly M. Wright, (301) 975-2166]

Recently Published

Nyyssonen, D., **Narrow-Angle Laser Scanning Microscope System for Linewidth Measurements on Wafers**, NISTIR 88-3808 (April 1989).

The integrated-circuit industry in its push to finer and finer line geometries approaching submicrometer dimensions has created a need for ever more accurate and precise feature-size measurements to establish tighter control of fabrication processes. In conjunction with the NBS Semiconductor Linewidth Metrology Program, a unique narrow-angle laser measurement system was developed. This report describes the theory, optical design, and operation of this system and includes computer software useful for characterizing the pertinent optical parameters and images for patterned thin layers. For thick layers, the physics is more complex, and only elements of the theory are included here. For more detail, the reader is referred to several related reports listed in the references.
[Contact: Beverly M. Wright, (301) 975-2166]

Postek, M.T., Keery, W.J., and Larrabee, R.D., **Specimen Biasing to Enhance or Suppress Secondary Electron Emission from Charging Specimens at Low Accelerating Voltages**, Journal of Scanning Microscopy, Vol. 11, pp. 111-121 (1989).

Specimen biasing is shown to produce improved images in the scanning electron microscope at low-beam energies (0.8 to 2.5 keV) when charging effects, topographic effects, or detector shadowing effects would otherwise be present. Examples of such improvement are given for gallium arsenide field-effect transistors (positive charging), patterned photoresist layers on silicon wafers (negative charging and shadowing in contact holes), fractured lucite (negative charging), polyethylene wrapper material (positive charging), and polished diamond tools (positive charging). It is concluded that specimen biasing may be a simpler and more convenient way to achieve some of the advantages of the converted backscattered secondary electron technique for imaging, but without some of the fundamental disadvantages of that technique. Characterization of this backscattered electron-derived image bears further investigation for possible metrological applications.
[Contact: Beverly M. Wright, (301) 975-2166]

Postek, M.T., Larrabee, R.D., and Keery, W.J., **An Approach to Accurate X-Ray Mask Measurements in a Scanning Electron Microscope**, NISTIR 89-4047 (January 1989).

This paper presents the concept and some preliminary experimental data on a new method for measuring critical dimensions on masks used for x-ray lithography. The method uses a scanning electron microscope in a transmitted-scanning electron microscope imaging mode and can achieve nanometer precision. Use of this technique in conjunction with measurement algorithms derived from electron-beam interaction modeling may ultimately enable measurements of these masks to be made to nanometer accuracy.
[Contact: Beverly M. Wright, (301) 975-

Dimensional Metrology (cont'd.)

2166]

Young, M., **Spatial Filtering Microscope for Linewidth Measurements**, Applied Optics, Vol. 28, No. 8, pp. 1467-1473 (15 April 1989).

High-pass filtering has been relatively little used in microscopy, yet it may have application to linewidth measurement and visualization of phase objects. A spatial-filtering microscope has been designed and built, entirely of conventional microscope objectives. For linewidth measurement, the spatial filter has an optimum width that allows linewidths to be measured within a few percent. Phase lines can also be examined, but phase-contrast microscopy may be more suited to weak phase objects such as integrated optical waveguides.
[Contact: Matt Young, (303) 497-3223/-5342]

Analysis Techniques

Released for Publication

Baghdadi, A., **Evaluation of Instrumental Correction Factors for Infrared Absorption Concentration Measurements**, to be published in the Proceedings of SPIE (The International Society for Optical Engineering, P.O. Box 20, Bellingham, WA 98227), 7th International Conference on Fourier Transform Spectroscopy, Fairfax, Virginia, June 19-23, 1989.

Infrared spectra obtained in a worldwide round-robin measurement of the oxygen content of silicon wafers were evaluated to determine whether instrumental correction factors could be derived from the spectrum of a silicon wafer polished on both sides. The data showed that each instrument could be characterized by its response at the oxygen level in the silicon absorption band. Three parameters were evaluated for possible use as calibration factors: the transmittance of the polished silicon at 2000 cm^{-1}, the absorption coefficient of the 610 cm^{-1} lattice absorption band, and the absorption coefficient of the 739 cm^{-1} lattice absorption band. However, no quantitatively consistent relationship was found between the measured oxygen content and any of these potential internal calibration factors.
[Contact: Aslan Baghdadi, (301) 975-2062]

Baghdadi, A., Scace, R.I., and Walters, E.J., **Semiconductor Measurement Technology: Database for and Statistical Analysis of the Interlaboratory Determination of the Conversion Coefficient for the Measurement of the Interstitial Oxygen Content of Silicon by Infrared Absorption**, to be published as NIST Special Publication 400-82.

This Special Publication contains the data collected for the worldwide, double-round-robin determination of the conversion coefficient used to calculate the interstitial oxygen content of silicon from infrared absorption measurements. It also contains detailed statistical analyses of those data. A paper describing the results of this study has been accepted for publication by the Journal of the Electrochemical Society. It should be considered the official result of the study. The approach taken to determine the conversion coefficient was to conduct interlaboratory round robins for both the infrared measurements and the absolute measurements. The infrared measurements were carried out at 18 laboratories in China, Europe, Japan, and the United States, using either dispersive infrared or Fourier transform infrared spectrometers. The absolute measurements were carried out at eight laboratories in Europe, Japan, and the United States, using either charged-particle activation analysis, photon activation analysis, or inert gas fusion analysis.
[Contact: Aslan Baghdadi, (301) 975-2062]

Rennex, B., **FTIR Determination of**

Analysis Techniques (cont'd.)

Interstitial Oxygen Concentration of Single-Side-Polished Silicon Wafers, to be published in the Proceedings of SPIE (The International Society for Optical Engineering, P.O. Box 20, Bellingham, WA 98227), 7th International Conference on Fourier Transform Spectroscopy Fairfax, Virginia, June 19-23, 1989.

This paper evaluates a new algorithm developed by the author for calculating interstitial oxygen concentration in silicon wafers, using infrared transmission data. These silicon wafers have an unpolished side and are referred to as being single-side-polished (SSP). This evaluation is carried out for various "unpolished" surface types, which are representative of etched or backside-damaged surfaces used by the integrated-circuit industry. In general, accurate measurement of oxygen content is necessary for improvement of quality control in the manufacture of integrated circuits; this process is more reliable and less costly if the measurements of oxygen concentration are carried out. A systematic offset in oxygen concentration is found for (100) caustic surfaces of surface category SC1. This offset is small (-1.5%), and it exhibits a small dispersion (sigma = 0.9%), when calculated with a new algorithm which features an interpolation procedure for the forward scattering parameter, F. This result is promising for development of a calibration approach for this surface category, which would have a 2-sigma uncertainty of about ±1.8%.
[Contact: Brian Rennex, (301) 975-2108]

Recently Published

Bouldin, C.E., Carter, A.C., Kirkland, J., and Neiser, R., **Silicon Photodiode Detectors for EXAFS**, Physica B, Vol. 158 (North-Holland, Amsterdam, 1989), pp. 339-341.

Results are shown of using a large-area silicon diode as a fluorescence detector for extended x-ray absorption fine-structure (EXAFS) measurements. A direct comparison of this diode detector relative to a gas ionization fluorescence detector is made. Advantages of the diode detector include: higher signal for a given photon flux (due to higher quantum efficiency), vacuum and cryogenic compatibility, freedom from microphonic noise, good linearity, extremely wide dynamic range, operation without high voltage or gas connections, very simple electronics, and low cost. Use of photodiodes for transmission EXAFS is discussed.
[Contact: Charles E. Bouldin, (301) 975-2046]

Photodetectors

Released for Publication

Geist, J., **Current Status of, and Future Directions in, Silicon Photodiode Self-Calibration.**

The current status of silicon photodiode self-calibration and its applications are reviewed, including the results of a number of intercomparisons that establish the suitability of self-calibration for high-accuracy metrology applications. Some current research directions known to the author are described, and possible future directions are considered.
[Contact: Jon Geist, (301) 975-2066]

Rasmussen, A.L., Sanders, A.A., and Simpson, P.A., **Improved Low-Level Silicon Avalanche Photodiode Transfer Standards at 1.064 Micrometers**, to be published as an NISTIR.

Three silicon avalanche photodiode transfer standards (APD TS) were calibrated from $\approx 10^{-8}$ to $\sim 10^{-5}$ W/cm^2 peak power density at approximately 10% uncertainty. Calibrations were performed for 1.064-μm wavelength pulses, having 10- to 100-ns durations. For this calibration, an acousto-optically modulated laser beam provided

Photodetectors (cont'd.)

alternately equal levels of pulsed power and cw power into a low-level beam splitter. The cw power measured by a transfer standard in the transmitted beam of the splitter was used to determine the pulsed power into the APD transfer standard in one of the low-level reflected beams of the splitter. The APD detector had about 1-cm^2 aperture and a 3.8-cm focal length lens in front of it. Lens, window, and detector surfaces had narrow-band anti-reflection coatings. The commercial detector package is a temperature-compensated, infrared-enhanced APD preamplifier module. To increase the sensitivity, one or two 20-dB, 500-MHz band-width amplifiers followed the preamplifier. At very low pulsed power levels, a 30-MHz low-pass filter with gaussian roll-off was attached to the amplifier output to reduce the noise. A transient digitizer recorded the impulse responses of the APD detectors at 1.064 μm. These data were read into computer programs that convolved the unity area impulse response with unity height gaussian pulses. From these data, correction factors of the pulse peak for observed pulse durations from 10 to 100 ns were determined. Instructions, calibrations, error budgets, and system descriptions are included.
[Contact: Alvin L. Rasmussen, (303) 497-5367]

Power Devices

Recently Published

Blackburn, D.L., **Power MOSFET Failure Revisited**, PESC '88 Record, Proceedings of the 1988 IEEE Power Electronics Specialists Conference, Kyoto, Japan, April 11-14, 1988, pp. 681-688 (1988).

The failure of power MOSFETs during avalanche breakdown is discussed. A theory is presented that relates the failure to the temperature rise of the chip during avalanche breakdown and to a critical current for failure. It is shown that the energy that can be safely dissipated during avalanche breakdown decreases as the starting current increases or as the case temperature increases. Thus, if power MOSFETs are to be rated for their energy dissipation capability during avalanche breakdown, both the starting current and temperature must be specified, as it is these two parameters that determine the failure limits.
[Contact: David L. Blackburn, (301) 975-2068]

Hefner, A.R., Jr., **An Improved Understanding for the Transient Operation of the Power Insulated Gate Bipolar Transistor (IGBT)**, PESC '89 Record, Proceedings of the 1989 IEEE Power Electronics Specialists Conference, Milwaukee, Wisconsin, June 26-29, 1989, pp. 303-313.

It is shown that a non-quasi-static analysis must be used to describe the transient current and voltage waveforms of the IGBT. The non-quasi-static analysis is necessary because the transports of electrons and holes are coupled for low-gain, high-level injection conditions, and because the quasi-neutral base width changes faster than the base transit speed for typical load circuit conditions. To verify that both of these non-quasi-static effects must be included, the results of quasi-static and non-quasi-static models are compared with measured current and voltage switching waveforms. The comparisons are performed for different load circuit conditions and for different device base lifetimes.
[Contact: Allen R. Hefner, Jr., (301) 975-2071]

Integrated Circuit Test Structures

Recently Published

Khera, D., Zaghloul, M.E., Linholm, L.W., and Wilson, C.L., **A Neural Network Approach for Classifying Test Structure Data**, Proceedings of ICMTS

IC Test Structures (cont'd.)

1989, International Conference on Microelectronic Test Structures, Edinburgh, Scotland, March 13-14, 1989, pp. 201-204.

This paper describes a new approach for identifying and classifying semiconductor manufacturing process variations using test structure data. The technique described in this paper employs a machine-learning algorithm based on neural networks to train computers to detect patterns associated with test structure results. The objective of this work is to develop more reliable machine-learning classification procedures using test structure data from a semiconductor manufacturing environment. An example based on characterizing the performance of a 1-μm lithography process is presented as well as a description of the test chip.
[Contact: Dheeraj Khera, (301) 975-2240]

Suehle, J.S., and Schafft, H.A., **The Electromigration Damage Response Time and Implications for dc and Pulsed Characterizations**, Proceedings of the 27th Annual International Reliability Physics Symposium, Phoenix, Arizona, April 10-13, 1989, pp. 229-233.

A new measurement interference for highly accelerated electromigration stress tests is identified. Measurements of the median-time-to-failure, t_{50}, for dc and for pulsed current stress as a function of frequency reveal that highly accelerated stress tests may overestimate metallization reliability if t_{50} is comparable with the response time of the vacancy concentration. Techniques necessary to make reliable wafer-level t_{50} measurements are described.
[Contact: John S. Suehle, (301) 975-2247]

Zaghloul, M.E., Khera, D., Linholm, L.W., and Reeve, C.P., **A Machine-Learning Classification Approach for IC Manufacturing Control Based on Test Structure Measurements**, IEEE Transactions on Semiconductor Manufacturing, Vol. 2, No. 2, pp. 47-53 (May 1989).

This paper describes the use of a machine-learning method for classifying electrical measurement results from a custom-designed test chip. These techniques are used for characterizing the performance of a 1-μm integrated circuit lithography process. The focus of the work is to develop a method for producing reliable classification rules from data bases containing large samples of measurement data. The paper describes a test chip, data-handling methods, rule generation techniques, and statistical data reduction and parameter extraction techniques. An analysis of error introduced by noise in the rule formation process is presented.
[Contact: Mona E. Zaghloul, (301) 975-2239]

Device Physics and Modeling

Released for Publication

Gaitan, M., Mayergoyz, I.D., and Korman, C.E., **Investigation of the Threshold Voltage of MOSFETs with Position and Potential Dependent Interface Trap Distributions Using a Fixed Point Method**.

Simulation results are presented for a MOSFET with position- and energy-(potential) dependent interface trap distributions which may be typical for devices subjected to interface trap-producing processes such as hot-electron degradation. The interface trap distribution is modeled as a Gaussian peak in a given position along the channel, while the energy dependence is derived from C-V measurements from an MOS capacitor exposed to ionizing radiation. A new fixed-point technique is used to solve for arbitrary distributions of interface traps. A comparison of the convergence properties of the Newton and fixed-point methods is pre-

Device Physics and Modeling (cont'd.)

sented, and it is shown that for some important cases, the Newton technique fails to converge while the fixed-point technique converges with a geometric rate.
[Contact: Michael Gaitan, (301) 975-2070]

Lowney, J.R., **The Effect of Electron-Hole Plasmas on the Density of States of Silicon and GaAs.**

The densities of states of the conduction and valence bands of silicon and GaAs have been calculated at 300 K for the case of an electron-hole plasma, which can occur at high-injection levels in bipolar devices or in bulk material under intense optical excitation. The results show considerable narrowing of the band gap, which needs to be included in the analysis of device measurements or the interpretation of photoluminescence data. Furthermore, the band-gap narrowing that results from dopant ions is reduced by excess carriers because of the reduced free-carrier screening radius.
[Contact: Jeremiah R. Lowney, (301) 975-2048]

Recently Published

Lowney, J.R., and Bennett, H.S., **Effects of Doping-Density Gradients on Band-Gap Narrowing in Silicon and GaAs Devices,** Journal of Applied Physics, Vol. 65, No. 12, pp. 4823-4827 (June 15, 1989).

The limitations of the theory for band-gap narrowing, which is based on uniform material, are considered in devices that have steep doping gradients. Validity criteria are derived that place upper bounds on the dopant and carrier density gradients for the application of the results from uniform theory. The existence of wavefunction tailing beyond the potential barriers that occur in devices is studied. At room temperature the effects due to these tails are usually small, but at low temperatures they can become very significant.
[Contact: Jeremiah R. Lowney, (301) 975-2048]

Insulators and Interfaces

Released for Publication

Marchiando, J.F., **Semiconductor Measurement Technology: A Software Program for Aiding the Analysis of Ellipsometric Measurements, Simple Models**, to be published as NIST Special Publication 400-83.

MAIN1 is a software program for aiding the analysis of ellipsometric measurements. MAIN1 consists of a suite of routines written in FORTRAN that are used to invert the standard reflection ellipsometric equations for simple systems. A system is said to be simple if the solid material sample may be adequately characterized by models which assume at least the following: 1) materials which are nonmagnetic; 2) samples which exhibit depth-dependent optical properties, such as layered or laminar structures atop a substrate that behaves like a semi-infinite half-space; 3) layers which are flat and of uniform thickness; and 4) a dielectric function within each layer/substrate which is isotropic, homogeneous, local, and linear. Each layer is characterized in part by a thickness (z), while the optical properties for a given material and wavelength are expressed in terms of a refractive index (n) and extinction coefficient (k). The ellipsometric equations are formulated as a standard damped nonlinear least-squares problem and then solved by an interactive method when possible. Estimates of the uncertainties associated with assigning numerical values to the model parameters are calculated as well.
[Contact: Jay F. Marchiando, (301) 975-2088]

Insulators and Interfaces (cont'd.)

Recently Published

Bouldin, C.E., **EXAFS Study of a Buried Germanium Layer in Silicon**, Physica B, Vol. 158 (North-Holland, Amsterdam, 1989) pp. 596-597.

EXAFS measurements are made of a 200 Å layer of Ge on a Si substrate. The Ge layer is covered by a 3000 Å layer of SiO_2. Sensitivity to the buried layer is enhanced through the use of grazing-incidence fluorescence detection. A two-channel photodiode detector is used to detect the fluorescence and to discriminate against Bragg peaks from the single-crystal Si substrate. Since the fluorescence signal is isotropic while the Bragg peaks are directional, one channel of the detector is always free of Bragg-peak interference. We determine the average number of Ge-Ge and Ge-Si neighbors in the buried Ge layer, the distances, and disorder in the first-shell. Prospects for studying the buried Ge-SiO_2 interface are discussed.
[Contact: Charles E. Bouldin, (301) 975-2046]

Dumin, D.J., Dabral, S., Freytag, M., Robertson, P.J., Carver, G.P., and Novotny, D.B., **High Mobility CMOS Transistors Fabricated on Very Thin SOS Films**, IEEE Transactions on Electron Devices, Vol. 36, No. 3, pp. 596-598 (March 1989).

The increased emphasis on submicron geometry CMOS/SOS devices has created a need for high-mobility CMOS transistors fabricated on high-quality films with thicknesses of the order of 0.1 to 0.2 μm. To date, the only demonstrated way of producing high-mobility transistors on very thin, high-quality SOS films in this thickness range has been to apply recrystallizations and regrowths to the films prior to transistor fabrication. It has been found that the mobility of CMOS transistors fabricated on very thin SOS films is a function of film growth rate. Transistors with mobilities nearly as high as those obtained on 1.0-μm thick films have been fabricated on SOS films 0.2 μm thick that have been grown at growth rates above 4 μm/min.
[Contact: Donald B. Novotny, (301) 975-2699]

Other Semiconductor Metrology Topics

Released for Publication

Kopanski, J.J., and Novotny, D.B., **Electrical Characterization of Beta Silicon Carbide MIS Capacitors with Thermally Grown or Chemical-Vapor-Deposited Oxides**, to be published as an Extended Abstract, Electrochemical Society Meeting, Hollywood, Florida, October 15-20, 1989.

Metal-Insulator-Semiconductor (MIS) capacitors were fabricated on beta silicon carbide single crystals. The insulating layers were thermally grown oxides or chemical-vapor-deposited oxides. Various oxidation conditions and post-deposition densification treatments were investigated. Capacitors were characterized by capacitance-voltage measurements. The effects of measurement frequency, voltage sweep rate, illumination, and temperature (to 300°C) on the C-V response were determined. Interface trap distributions were estimated from the high-frequency capacitance. Oxide fixed charges were 5 to 9 x 10^{11} cm^{-2}, and interface trapped charge density at mid-gap levels was 0.5 to 2.0 x 10^{11} cm^{-2} eV^{-1}.
[Contact: Joseph J. Kopanski, (301) 975-2089]

Recently Published

Bouldin, C.E., Bunker, G., McKeown, D.A., Ritter, J.J., and Forman, R.A., **Multiple Scattering in the XANES** (X-ray Absorption Near Edge Structure) **of Tetrahedral Germanium Gases**, Physica B, Vol. 158 (North-Holland, Amsterdam, 1989), pp. 362-364.

Other Semiconductor Topics (cont'd.)

X-ray absorption fine-structure (XAFS or EXAFS (E = Extended)) measurements of $GeCl_4$, GeH_3Cl, and GeH_4 are reported. Since wide-angle multiple scattering (MS) involving H atoms is negligible, we experimentally isolate the single and MS terms in the XAFS of $GeCl_4$ by comparison of the spectra of the three compounds. We find that MS is nowhere dominant over single scattering (SS), although within 15 eV of the edge the two are comparable in size. However, the MS damps out very quickly with increasing energy above the absorption edge. Beyond 40 eV past the edge the MS/SS ratio is less than 0.06. Our calculations are found to be in qualitative agreement with experiment, but overestimate the size and energy range of the MS. Our results suggest that XAFS data in the range $1 < K < 3$ $Å^{-1}$ can be analyzed in an SS picture in many cases, as long as good standard compounds are used, and calculations are used to estimate possible errors due to neglect of MS. We also report the first evidence of single scattering observed from H atoms.
[Contact: Charles E. Bouldin, (301) 975-2046]

SIGNALS & SYSTEMS METROLOGY PROGRAM

FAST SIGNAL ACQUISITION, PROCESSING, AND TRANSMISSION

Waveform Metrology

Released for Publication

McKnight, R.H., Lagnese, J., and Zhang, Y., **Characterizing Transient Measurements By Use of the Step Response and the Convolution Integral.**

The convolution integral is used with experimentally determined step responses and analytic waveforms which represent modifications to ideal waveforms expected in an experimental arrangement to determine the suitability of a given system for measuring waveforms of interest. Examples of the application of the method to specific measuring systems are presented.
[Contact: John Lagnese, (301) 975-2423]

Zhang, Y.X., McKnight, R.H., and Fenimore, C., **A Method for Fitting and Smoothing Digital Data**, to be published in the Proceedings of the 6th International Symposium on High Voltage Engineering, New Orleans, Louisiana, August 28-September 1, 1989.

A method has been developed and evaluated to fit and smooth digital data using cubic splines. Most high-voltage waveforms cannot be fit by a simple analytic expression. Therefore, piecewise fitting is needed. Calculation shows that the fitting algorithm is suitable for the full-lightning and chopped lightning waveforms and the step response. A criterion for selecting the principal free parameter in the fitting process is given with an example.
[Contact: Charles Fenimore, (301) 975-2428]

Recently Published

Oldham, N.M., Hetrick, P.S., and Xiangren, Z., **A Calculable, Transportable Audio-Frequency AC Frequency Standard**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 368-371 (April 1989). [Also published in the Conference Digest of CPEM '88, 1988 Conference on Precision Electromagnetic Measurements, Tsukuba Science City, Japan, June 7-10, 1988, pp. 46-47 (IEEE, New York, New York, June 1988).]

A transportable ac voltage source is described, in which sinusoidal signals are digitally synthesized in the audio-frequency range. The rms value of the output waveform may be calculated by measuring the dc level of the individual steps used to generate the waveform. The uncertainty of this calculation at the 7-V level is typically less than ±5 ppm from 60 Hz to 2 kHz and less than ±10 ppm from 30 Hz to 15 kHz.

Waveform Metrology (cont'd.)

[Contact: Nile M. Oldham, (301) 975-2408]

Oldham, N.M., Petersons, O., and Waltrip, B.C., **Audio-Frequency Current Comparator Power Bridge: Development and Design Considerations**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 390-394 (April 1989). [Also published in the Conference Digest of CPEM '88, 1988 Conference on Precision Electromagnetic Measurements, Tsukuba Science City, Japan, June 7-10, 1988, p. 48 (IEEE, New York, New York, June 1988)].

The development, design, construction, and partial evaluation of a system for performing active and reactive power measurement from 50 to 20 kHz is described. The technique is an extension of a power bridge based on a current comparator capacitance bridge that was originally restricted to power frequencies. The design features and component characteristics for wide-band operation are emphasized. A digitally synthesized, dual-channel signal source provides the required voltage and current signals.
[Contact: Nile M. Oldham, (301) 975-2408]

Souders, M.T., and Hetrick, P.S., **Accurate RF Voltage Measurements Using a Sampling Voltage Tracker**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 451-456 (April 1989). [Also published in the Conference Digest of CPEM '88, 1988 Conference on Precision Electromagnetic Measurements, Tsukuba Science City, Japan, June 7-10, 1988, pp. 270-271 (IEEE, New York, New York, June 1988).]

The radio-frequency (rf) voltage measurement capability of an equivalent time-sampling system is described. The frequency range investigated is 1 to 100 MHz. Over this range, the measured errors, determined by ac/dc thermal transfer, are within the stated uncertainties presently provided by NIST for thermal converter calibrations. The system offers several advantages over conventional thermal transfer techniques: ac/dc transfers are not required, loading and transmission line problems are reduced, and direct measurement of voltages from 2 V to as low as 10 mV are possible.
[Contact: T. Michael Souders, (301) 975-2406]

Cryoelectronic Metrology

Released for Publication

Kautz, R.L., **Design and Operation of Series-Array Josephson Voltage Standards**, to be published in the Proceedings of the International School of Physics, "Enrico Fermi," Course CX, Lerico, Italy, June 27-July 7, 1989.

Series arrays typically including 1500 Josephson junctions driven at 90 GHz have been used to generate quantized reference voltages in excess of 10 V. Such standards simplify the procedure and reduce the measurement uncertainties in the calibration of electrochemical cells.
[Contact: Richard L. Kautz, (303) 497-3391]

Martinis, J.M., and Kautz, R.L., **Classical Phase Diffusion in Small Hysteretic Josephson Junctions.**

The existence of classical phase diffusion in hysteretic junctions is demonstrated by quantitative agreement between experimental and simulated I-V curves. The simulations are based on a circuit that accurately models both the junction and its external shunting impedance at microwave frequencies. A previous analysis of diffusion in underdamped junctions is shown to be incomplete because it fails to account for multiple-phase-slip events.
[Contact: John M. Martinis, (303) 497-3597]

Sutton, E.C., Danchi, W.C., Jaminet,

Cryoelectronic Metrology (cont'd.)

P.A., and Ono, R.N., **A Superconducting Tunnel Junction Receiver for 345 GHz.**

In this paper we discuss the design, fabrication, and testing of a quasiparticle tunnel junction receiver for use at 345 GHz. The design employs small-area Nb edge junctions in order to keep the device capacitance small and maintain a modest value for the product of frequency, junction normal-state resistance, and junction capacitance. For optimum noise performance and beam properties, the mixer is contained in a waveguide mounting structure. Our best sensitivity was obtained at 312 GHz where we measured a double sideband noise temperature of 275 K. Good sensitivity was obtained out to 360 GHz.
[Contact: Ronald H. Ono, (303) 497-3762]

Recently Published

Danchi, W.C., Sutton, E.C., Jaminet, P.A., and Ono, R.H., **Nb Edge Junction Process for Submillimeter Wave SIS Mixers**, IEEE Transactions on Magnetics, Vol. 25, No. 2, pp. 1064-1067 (March 1989). [A separate paper by the same authors, **A Superconducting Tunnel Junction Receiver for 345 GHz**, has been approved by NIST for publication.]

We describe a junction fabrication process that produces high-quality Nb edge junctions of areas less than 0.2 μm^2 on thin quartz (0.10-mm) substrates. This process utilizes a 10:1 projection wafer stepper for high resolution and high-accuracy layer-to-layer registration. We have fabricated large numbers of junctions reliably with high-quality I-V characteristics and with impedances suitable for use in SIS mixers for submillimeter astronomy. Junctions produced by this process can be stored on the shelf for more than two years with no special precautions taken, and with an impedance change of less than 10%. No failures have been observed after thermal cycling. Currently, these junctions are being used in an astronomical receiver that demonstrates state-of-the-art performance in the atmospheric window centered at 345 GHz. With some improvements to the process, it is possible to make junctions with areas sufficiently small so that the product of frequency, junction normal-state resistance, and junction capacitance is about 3 at 800 GHz.
[Contact: Ronald H. Ono, (303) 497-3762]

Moreland, J., Ono, R.H., Beall, J.A., Madden, M., and Nelson, A.J., **Evidence for the Superconducting Proximity Effect in Junctions Between the Surfaces of $YBa_2Cu_3O_x$ Thin Films** [original title: Superconducting Proximity Contacts Between the Surfaces of $YBa_2Cu_3O_x$ Thin Films], Appl. Phys. Lett., Vol. 54, No. 15, pp. 1477-1479 (10 April 1989).

We use the squeezable electron tunneling (SET) junction technique for testing the superconducting properties of the surfaces of $YBa_2Cu_3O_x$ (YBCO) thin-film electrodes. The I-V characteristics of the SET junctions indicate that superconductor/normal metal/superconductor contacts exist between the surfaces of the electrodes when they are allowed to touch each other. As deposited and annealed, the surfaces of the electrodes are not superconducting at 4 K. Several methods are used to improve the superconducting properties of the surfaces of the electrodes, including rapid thermal annealing, oxygen sputter etching, and thin-silver coating treatments. The greatest improvement occurs after deposition of a 5-nm Ag coating and subsequent rapid thermal anneal of the YBCO film. Under these conditions, it is possible to make a superconducting Josephson point contact between the surfaces of the electrodes. We believe that the Ag acts as a normal-metal proximity layer effectively bridging the degraded surfaces of the electrodes.
[Contact: John Moreland, (303) 497-3641]

Electro-Optic Metrology

Released for Publication

Deeter, M.N., Rose, A.H., and Day, G.W., **Characteristics of Polarimetric Magnetic Field Sensors Based on Yttrium Iron Garnet**, to be published in the Technical Digest of the 1989 LEOS (Lasers and Electro-Optics Society, IEEE) Meeting, Orlando, Florida, October 17-20, 1989.

We describe the performance characteristics of polarimetric Faraday-effect magnetic field sensors employing ferrimagnetic sensing elements, such as yttrium iron garnet (YIG). Experimental results of sensor sensitivity, linearity, and directionality are presented for three cylindrical YIG samples, each having a different length-to-width ratio.
[Contact: Merritt N. Deeter, (303) 497-5400]

Ghatak, A.K., Goyal, I.C., and Gallawa, R.L., **Mean Lifetime Calculations of Quantum Well Structures: A Rigorous Analysis.**

A matrix method is described which will be applicable to an arbitrary potential variation represented by a set of linear functions, e.g., multiple-quantum-well structures in the presence of a static electric field. An analytical expression for the mean lifetime of the quasi-bound state of a single quantum well in the presence of a static electric field has been obtained.
[Contact: Robert L. Gallawa, (303) 497-3761]

Goyal, I.C., Gallawa, R.L., and Ghatak, A.K., **A New Method of Analyzing Bent Planar Waveguides Including the Effect of Whispering Gallery Modes.**

A new matrix method is used to analyze bent planar optical waveguides. The method is a modification of the numerical analysis matrix method for planar waveguides developed by Ghatak and colleagues at the Indian Institute of Technology, New Delhi (IIT), and may be used with absorbing or leaky structures. The new method is a refinement in that a nonuniform refractive index is approximated by a series of linear profiles rather than by a series of uniform profiles. The method is used to analyze a bent planar waveguide, yielding bend loss directly. The effect of "whispering-gallery" modes has also been studied. The new results suggest that the whispering-gallery explanation advanced previously by the IIT team may not be adequate.
[Contact: Robert L. Gallawa, (303) 497-3761]

Rasmussen, A.L., Sanders, A.A., and Simpson, P.A., **Improved Low-Level Silicon Avalanche Photodiode Transfer Standards at 1.064 Micrometers**, to be published as an NISTIR.

Three silicon avalanche photodiode transfer standards (APD TS) were calibrated from $\approx 10^{-8}$ to $\sim 10^{-5}$ W/cm^2 peak power density at approximately 10% uncertainty. Calibrations were performed for 1.064-μm wavelength pulses, having 10- to 100-ns durations. For this calibration, an acousto-optically modulated laser beam provided alternately equal levels of pulsed power and cw power into a low-level beam splitter. The cw power measured by a transfer standard in the transmitted beam of the splitter was used to determine the pulsed power into the APD transfer standard in one of the low-level reflected beams of the splitter. The APD detector had about 1-cm^2 aperture and a 3.8-cm focal length lens in front of it. Lens, window, and detector surfaces had narrow-band anti-reflection coatings. The commercial detector package is a temperature-compensated, infrared-enhanced APD preamplifier module. To increase the sensitivity, one or two 20-dB, 500-MHz band-width amplifiers followed the preamplifier. At very low pulsed power levels, a 30-MHz low-pass filter with gaussian roll-off was attached to the

Electro-Optic Metrology (cont'd.)

amplifier output to reduce the noise. A transient digitizer recorded the impulse responses of the APD detectors at 1.064 μm. These data were read into computer programs that convolved the unity area impulse response with unity height gaussian pulses. From these data, correction factors of the pulse peak for observed pulse durations from 10 to 100 ns were determined. Instructions, calibrations, error budgets, and system descriptions are included.
[Contact: Alvin L. Rasmussen, (303) 497-5367]

Schlager, J.B., Yamabayashi, Y., Franzen, D.L., and Juneau, R.I., **Fundamental Mode-Locked Long Cavity Erbium Fiber Lasers with Subsequent Soliton Compression.**

Erbium fiber lasers with cavity lengths of 5 to 5000 m are mode-locked at the fundamental cavity frequency using an integrated-optic intensity modulator driven by a novel pulse generator. Resulting optical pulses at 1536 nm are recorded with a synchro-scan streak camera and have durations of 18 to 80 ps with peak powers over 6 W. The shorter cavity lengths yield transform-limited pulses which are narrowed by soliton-like compression to approximately 5 ps after propagation through an external 14-km fiber.
[Contact: John B. Schlager, (303) 497-3542]

Recently Published

Day, G.W., and Rose, A.H., **Faraday Effect Sensors: The State of the Art,** Proceedings of SPIE (The International Society for Optical Engineering, P.O. Box 20, Bellingham, WA 98227), Vol. 985, Fiber Optic & Laser Sensors VI, pp. 138-150 (1988).

The Faraday effect is becoming widely used as an optical method of measuring electric current or magnetic field. It is particularly advantageous where the measurements must be made at high voltage or in the presence of electromagnetic interference, and where speed or stability are considerations. In this paper we review the development of the technology over the last twenty years, with an emphasis on the basic principles, design considerations, and performance capabilities of sensors that represent the latest achievements. Faraday effect current sensors are now used routinely in the measurement of large current pulses, and are starting to become available for ac current measurements in the power industry. Recent developments include their extension to the measurement of currents in the milliampere range and substantial reductions in size. Similar devices, in slightly different configurations, can be used for magnetic field measurements. Further improvements, based on new fiber types and new materials, are projected.
[Contact: Gordon W. Day, (303) 497-5204]

Hickernell, R.K., Larson, D.R., Phelan, R.J., Jr., and Larson, L.E., **Waveguide Loss Measurement Using Photothermal Deflection**, Applied Optics, Vol. 27, No. 13, pp. 2636-2638 (July 1, 1988).

Photothermal deflection (PTD) is introduced as a technique for measuring propagation loss in optical channel waveguides. A probe laser beam is deflected by the thermally induced refractive-index gradient due to the absorption of guided pump light. The technique is noncontact and is applicable to a wide range of channel waveguide geometries and materials, including buried guides. Scattering centers and unguided background light affect the measurement only indirectly, since the PTD signal depends on the gradient of the local temperature and not the light intensity directly.

The pump beam from a HeNe laser of 633-nm wavelength was mechanically chopped and coupled into potassium, ion-exchanged, glass waveguides. The probe beam, also of 633-nm wavelength, was

Electro-Optic Metrology (cont'd.)

focused on the substrate surface, and its deflection was measured by a silicon bicell using lock-in detection. Our measurements of the PTD signal as a function of the probe spot position agree with similar measurements performed on bulk materials by other researchers. Scans of the PTD signal as a function of distance along the waveguide yielded propagation loss measurements with lower uncertainty than scans of the scattered light intensity. The PTD technique should be useful in the study of waveguide loss mechanisms.
[Contact: Robert K. Hickernell, (303) 497-3455]

DC and Low Frequency Metrology

Recently Published

Field, B.F., and McCaleb, M.R., **An Improved Transportable DC Voltage Standard**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 324-329 (April 1989).

Zener-diode-based dc voltage standards can be excellent transport standards for the unit of dc voltage because of their resistance to physical shock and temperature changes. The problems of transporting a unit of voltage and the properties of available Zener standards were studied to develop a set of characteristics that we consider to be essential for an optimum transport standard. We report some of the results of this requirements study, explain the design of our improved transport standard, discuss our efforts to select Zener diodes for the standard, and present data obtained from prototype Zener reference modules to be used in the standard.
[Contact: Bruce F. Field, (301) 975-4230]

Steiner, R.L., and Field, B.F., **Josephson Array Voltage Calibration System Operational Use and Verification**, IEEE Transactions on Instrumentation and Measurement, Vol.. 38, No. 2, pp. 296-301 (April 1989).

A new Josephson array system now maintains the U.S. Legal Volt. This system is almost fully automated, operates with a typical precision of 0.009 μV, and readily allows U.S. Legal Volt measurements weekly, or more frequently if desired. This system was compared to the previous volt maintenance system, and agreement was achieved to within 0.03 ppm. This verification is limited by uncertainties in the resistive-divider instruments of the previous system.
[Contact: Richard L. Steiner, (301) 975-4226]

Fundamental Electrical Measurements

Released for Publication

Cage, M.E., Van Degrift, C.T., and Yu, D., **Observation and an Explanation of Breakdown of the Quantum Hall Effect.**

We observe spatially localized breakdown of the nearly dissipationless quantum Hall effect regime into a set of discrete dissipative states in wide, high-quality GaAs/AlGaAs samples. The phenomenon can be explained by quasi-elastic inter-Landau level scattering. We propose the existence of a new, highly efficient population inversion mechanism and the possible existence of an acoustic phonon laser.
[Contact: Marvin E. Cage, (301) 975-4248]

Van Degrift, C.T., Cage, M.E., and Girvin, S.M., **Resource Letter QHE-1: The Integral and Fractional Quantum Hall Effects.**

This Resource Letter provides a guide to the literature on the integral and fractional quantum Hall effects. The letter E after an item indicates elementary level or material of general interest to persons becoming informed in the field. The letter I, for intermediate level, indicates material of

Fundamental Electrical Meas. (cont'd.)

somewhat more specialized nature; and the letter A indicates rather specialized or advanced material. An asterisk (*) indicates articles that we feel are especially useful or interesting; a double asterisk (**) indicates those articles to be included in an accompanying reprint book.
[Contact: Craig T. Van Degrift, (301) 975-4248]

Williams, E.R., Sheng, Y., Olsen, P.T., Elmquist, R.E., Ruimin, L., and Jones, G.R., Jr., **Latest Results of the Proton Gyromagnetic Ratio in Water Plus Related Experiments**, to be published in the Conference Proceedings of the International Symposium on Electromagnetic Metrology, Beijing, China, August 17-22, 1989.

We present the details of our latest measurement of the proton gyromagnetic ratio γ_p'(low), and the resultant value of the quantum Hall resistance, R_H, and the fine structure constant, α. A discussion is included of possible sources for the discrepancy of -0.102 ± 0.043 ppm between the absolute ohm and this measurement, along with a method to measure h/e^2 by counting electrons in a storage ring.
[Contact: Edwin R. Williams, (301) 975-6555]

Recently Published

Belecki, N.B., Dziuba, R.F., Field, B.F., and Taylor, B.N., **Guidelines for Implementing the New Representations of the Volt and Ohm Effective January 1, 1990**, NIST Technical Note 1263 (June 1989).

This document provides general guidelines and detailed instructions on how to bring laboratory reference standards of voltage and resistance and related instrumentation into conformity with newly established and internationally adopted representations of the volt and ohm. Based on the Josephson and quantum Hall effects, respectively, the new representations are to come into effect worldwide starting on January 1, 1990. Their implementation in the United States will result in increases in the values of the national volt and ohm representations maintained at the National Institute of Standards and Technology of 9.264 parts per million (ppm) and 1.69 ppm, respectively. The resulting increase in the value of the U.S. representations of the ampere will be about 7.57 ppm and in the U.S. electrical representation of the watt, about 16.84 ppm. Also discussed are the effects on electrical standards of the January 1, 1990, replacement of the International Practical Temperature Scale of 1968 by the International Temperature Scale of 1990; and of the January 1, 1990, approximate 0.14-ppm decrease in the U.S. representation of the farad.
[Contact: Norman B. Belecki, (301) 975-4223]

Cage, M.E., Dziuba, R.F., Elmquist, R.E., Field, B.F., Jones, G.R., Jr., Olsen, P.T., Phillips, W.D., Shields, J.Q., Steiner, R.L., Taylor, B.N., and Williams, E.R., **NIST Determination of the Fine-Structure Constant, and of the Quantized Hall Resistance and Josephson Frequency to Voltage Quotient in SI Units**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 284-289 (April 1989).

Results from NIST experiments to realize the ohm and the watt, to determine the proton gyromagnetic ratio and the time dependence of the NIST ohm using the quantum Hall effect, and to maintain the NIST volt using the Josephson effect are appropriately combined to obtain an accurate value of the fine-structure constant and of the quantized Hall resistance in SI units, and values in SI units of the Josephson frequency to voltage quotient, Planck constant, and elementary charge.
[Contact: Barry N. Taylor, (301) 975-4220]

Fundamental Electrical Meas. (cont'd.)

Cage, M.E., Dziuba, R.F., Van Degrift, C.T., and Yu, D., **Determination of the Time-Dependence of Ω_{NBS} Using the Quantized Hall Resistance**, IEEE Transactions of Instrumentation and Measurement, Vol. 38, No. 2, pp. 263-269 (April 1989).

The quantum Hall effect is being used to monitor the U.S. legal representation of the ohm, or as-maintained ohm, Ω_{NBS}. Measurements have been made on a regular basis since August 1983. Individual transfers between the quantized Hall resistance R_H and the five 1-Ω resistors which comprise Ω_{NBS} can now be made with a total one standard deviation (1σ) uncertainty of ±0.014 ppm. This uncertainty is the root-sum-square of 32 individual components. The time-dependent expression for R_H in terms of Ω_{NBS} is: $R_H = 25\ 812.8[1 + (1.842 \pm 0.012) \times 10^{-6} + (0.0529 \pm 0.0040)(t-0.7785) \times 10^{-6}/\text{year}]\Omega_{NBS}$, where t is measured in years from January 1, 1987. The value of Ω_{NBS} is, therefore, decreasing at the rate of (0.0529 ± 0.0040) ppm/year.
[Contact: Marvin E. Cage, (301) 975-4248]

Olsen, P.T., Elmquist, R.E., Phillips, W.D., Williams, E.R., Jones, G.R. Jr., and Bower, V.E., **A Measurement of the NBS Electrical Watt in SI Units**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 238-244 (April 1989).

We have measured the NBS (now NIST) electrical watt in SI units to be: $W_{NIST}/W = K_W = 1 - (16.69 \pm 1.33)$ ppm. The uncertainty of 1.33 ppm has the significance of a standard deviation and includes our best estimate of random and known or suspected systematic uncertainties. The mean time of the measurement is 15 May 1988. Combined with the recent measurement of the NIST ohm in SI units: $\Omega_{NIST}/\Omega = K_\Omega = 1 - (1.593 \pm 0.022)$ ppm, this leads to a Josephson frequency/voltage quotient of $E_J = E_o$ [1 + (7.94 ± 0.67) ppm] where E_o = 483594 GHz/V.
[Contact: P. Thomas Olsen, (301) 975-6553]

Shields, J.Q., Dziuba, R.F., and Layer, H.P., **New Realization of the Ohm and Farad Using the NBS Calculable Capacitor**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 249-251 (April 1989).

Results of a new realization of the ohm and farad using the NBS calculable capacitor and associated apparatus are reported. The results show that both the NBS representation of the ohm and the NBS representation of the farad are changing with time, Ω_{NBS} at the rate of -0.054 ppm/year and F_{NBS} at the rate of 0.010 ppm/year. The realization of the ohm is of particular significance at this time because of its role in assigning an SI value to the quantized Hall resistance. The estimated uncertainty of the ohm realization is 0.022 ppm (1σ), while the estimated uncertainty of the farad realization is 0.014 ppm (1σ).
[Contact: John Q. Shields, (301) 975-4223]

Williams, E.R., Jones, G.R. Jr., Sheng, Y., Liu, R., Sasaki, H., Olsen, P.T., Phillips, W.D., and Layer, H.P., **A Low Field Determination of the Proton Gyromagnetic Ratio in Water**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 233-237 (April 1989).

We measure the proton gyromagnetic ratio in H_2O by the low-field method, γ_p'(low). The result, $\gamma_p'(\text{low}) = 2.67513376\ 10^8\ s^{-1}\ T_{NIST}^{-1}$ (0.11 ppm), leads to a value of the fine structure constant of α^{-1} = 137.0359840 (0.037 ppm) and a value for the quantized Hall resistance in SI units of R_H = 25812.80460 Ω (0.037 ppm). To achieve this result, we measured the dimensions of a 2.1-m solenoid with an accuracy of 0.04 μm, and then measured the NMR frequency of a water sample in the field of the solenoid.

Fundamental Electrical Meas. (cont'd.)

[Contact: Edwin R. Williams, (301) 975-6555]

ELECTRICAL SYSTEMS

Power Systems Metrology

Released for Publication

Martzloff, F.D., **Lightning and Surge Protection of Photovoltaic Installations, Two Case Histories: Vulcano and Kythnos**, to be published as NISTIR 89-4113.

Two installations of photovoltaic power-supply systems were damaged during lightning storms. The two sites were visited and the damaged equipment that was still available on the site was examined for analysis of the suspected occurrence. The evidence, however, is insufficient to conclude that all the observed damage was caused by the direct effect of lightning. A possible scenario may be that lightning-induced overvoltages caused insulation breakdown at the edges of the photovoltaic modules, with subsequent damage done by the dc current of the array. Surge protection considerations are addressed, and suggestions presented for further investigations.
[Contact: Francois D. Martzloff, (301) 975-2409]

Olthoff, J.K., Van Brunt, R.J., and Sauers, I., **Electron Energy Dependence of the S_2F_{10} Mass Spectrum.**

The positive ion mass spectrum of S_2F_{10} has been measured as a function of electron-impact energy in the range 20 to 70 eV using a quadrupole mass spectrometer. Contrary to recent results reported by Farber and coworkers (1989) from mass spectrometric analysis of arc-decomposed SF_6, there was no evidence of $S_2F_9^+$ or $S_2F_{10}^+$ ion formation from S_2F_{10} at any energy. The largest ion observed at all electron energies is SF_5^+. It was found, however, that the appearance potentials for SF_5^+ and SF_3^+, the two most prominent ions from S_2F_{10}, are significantly lower than the appearance potentials of these same ions from SF_6. The differences between the mass spectra of S_2F_{10} and SF_6 are delineated, and the implications for detection of S_2F_{10} in the presence of SF_6 are discussed.
[Contact: James K. Olthoff, (301) 975-2431]

Van Brunt, R.J., Herron, J.T., Sauers, I., Siddagangappa, M.C., and Harman, G., **Production and Stability of S_2F_{10} in SF_6 Corona Discharges**, to be published in the Proceedings of the 6th International Symposium on High Voltage Engineering, New Orleans, Louisiana, August 28-September 1, 1989.

We report the yield of S_2F_{10} produced in corona discharges in SF_6 and the dependence of the S_2F_{10} yield on various parameters. The data were obtained from two experimental systems, both employing point-to-plane geometry: (1) a small corona cell (milliliters in volume 200) with a gas chromatograph-thermal conductivity analyzer at Oak Ridge National Laboratory and (2) a large (3.7-liter) corona cell with a gas chromatograph-mass spectrometer (GC-MS) analyzer at NIST. The GC-MS technique was found to be quite sensitive to S_2F_{10} when the mass analyzer was tuned to mass 86 (SOF_2^+). The mechanism for conversion of S_2F_{10} into SOF_2 at the end of the GC column is not yet understood. In both experiments, the concentration of S_2F_{10} increased linearly with time. However, the charge rate-of-production appeared to depend on uncontrollable factors such as moisture content. Although the thermal decay of S_2F_{10} is predicted to be very slow (10^7-year half-life at 23°C), surface processes may account for an increase in the S_2F_{10} decomposition rate.
[Contact: Richard J. Van Brunt, (301) 975-2425]

Zhang, Y.X., McKnight, R.H., and Fenimore, C., **A Method for Fitting and**

Power Systems Metrology (cont'd.)

Smoothing Digital Data, to be published in the Proceedings of the 6th International Symposium on High Voltage Engineering, New Orleans, Louisiana, August 28-September 1, 1989.

A method has been developed and evaluated to fit and smooth digital data using cubic splines. Most high-voltage waveforms cannot be fit by a simple analytic expression. Therefore, piecewise fitting is needed. Calculation shows that the fitting algorithm is suitable for the full-lightning and chopped lightning waveforms and the step response. A criterion for selecting the principal free parameter in the fitting process is given with an example.
[Contact: Charles Fenimore, (301) 975-2428]

Recently Published

Anderson, W.E., **Calibration of Voltage Transformers and High-Voltage Capacitors at NIST**, Journal of Research of the National Institute of Standards and Technology, Vol. 94, No. 3, pp. 179-195 (May-June 1989).

The National Institute of Standards and Technology (NIST) calibration service for voltage transformers and high-voltage capacitors is described. The service for voltage transformers provides measurements of ratio correction factors and phase angles at primary voltages up to 170 kV and secondary voltages as low as 10 V at 60 Hz. Calibrations at frequencies from 50 to 400 Hz are available over a more limited voltage range. The service for high-voltage capacitors provides measurements of capacitance and dissipation factor at applied voltages ranging from 100 V to 170 kV at 60 Hz depending on the nominal capacitance. Calibrations over a reduced voltage range at other frequencies are also available. As in the case with voltage transformers, these voltage constraints are determined by the facilities at NIST.
[Contact: William E. Anderson, (301) 975-2423]

McComb, T.R., Hughes, R.C., Lightfoot, H.A., Schon, K., Schulte, R., McKnight, R.H., and Zhang, Y.X., **International Comparison of HV Impulse Measuring Systems**, IEEE Transactions on Power Delivery, Vol. 4, No. 2, pp. 906-915 (April 1989).

Present standards for qualifying high voltage (HV) impulse measuring systems by unit-step-response parameters are complex and difficult to apply, and some systems, which have response parameters within the limits of the standards, have unacceptable errors. This paper takes the first step in providing a simplified method based on simultaneous measurements of an HV impulse by a reference system and the system under test. Comparative measurements have been made in four national laboratories, and the relative differences are reported. The results are discussed and the further work which is required is outlined.
[Contact: John Lagnese, (301) 975-2423]

Misakian, M., **Discussion of Paper 88 SM 560-5, "Performance of a Long-Term Unattended Station for Measuring DC Fields and Air Ions from an Operating HVDC Line," by V.L. Chartier, L.D. Dickson, L.Y. Lee, and R.D. Stearns**, IEEE Transactions on Power Delivery, Vol. 4, No. 2, p. 1328 (April 1989).

This discussion refers to a paper presented at the IEEE Power Engineering Society 1988 summer meeting in Portland, Oregon.
[Contact: Martin Misakian, (301) 975-2426]

Misakian, M., Anderson, W.E., and Laug, O.B., **Drift Tubes for Characterizing Atmospheric Ion Mobility Spectra Using AC, AC-Pulse, and Pulse Time-of-Flight Measurement Techniques**, Rev. Sci. Instrum., Vol. 60, No. 4, pp. 720-729 (April 1989).

Power Systems Metrology (cont'd.)

Two drift tubes constructed of insulating cylinders with conductive guard rings on the inside walls were examined to determine their suitability for measuring ion mobility spectra at atmospheric pressure. One drift tube is of the pulse time-of-flight (TOF) type with adjustable drift distance, and the other is an ac-TOF drift tube similar in principle to a device reported by Van de Graaff. The latter tube was evaluated using sinusoidal and alternating-polarity pulse-voltage waveforms for gating the shutters.
[Contact: Martin Misakian, (301) 975-2426]

Moore, W.J.M., So, E., Oldham, N.M., Miljanic, P.N., and Bergeest, R., **An International Comparison of Power Meter Calibrations Conducted in 1987**, IEEE Transactions on Instrumentation and Measurement, Vol. 38, No. 2, pp. 395-401 (April 1989). [Also published in the Conference Digest of CPEM'88, 1988 Conference on Precision Electromagnetic Measurements, Tsukuba Science City, Japan, June 7-10, 1988, pp. 341-342 (IEEE, New York, New York, June 1988)].

The results of an intercomparison of power meter calibrations conducted during 1987 between the National Research Council, Ottawa, the National Bureau of Standards (now the National Institute of Standards and Technology), Gaithersburg, the Physikalisch-Technische Bundesanstalt, Braunschweig, and the Institut Mihailo Pupin, Belgrade, are described. The comparison was implemented by a transfer standard consisting of a time-division multiplier watt-converter developed at the Institut Mihailo Pupin. The measurements were made at 120 V, 5 A, 50 and 60 Hz, at power factors of 1.0, 0.5 lead and lag, and 0.0 lead and lag. An agreement between the laboratories of better than 20 ppm is indicated.
[Contact: Nile H. Oldham, (301) 975-2408]

Zhang, Y.X., McKnight, R.H., and Hebner, R.E., **Interactions Between Two Dividers Used in Simultaneous Comparison Measurements**, IEEE Transactions on Power Delivery, Vol. 4, No. 3, pp. 1586-1594 (July 1989).

A revised international standard for the measurement of lightning and front-chopped lightning impulses is presently under consideration. This standard states that the accuracy of the measuring systems used is to be determined by comparison to reference systems maintained by appropriate national laboratories. Investigations have been made of the interactions between two systems configured for simultaneous measurements and of methods for minimizing these interactions. Unit step responses were measured for different configurations, and a model developed to predict divider response. Simultaneous measurements were made of full and chopped lightning impulses using different divider systems to determine the effects of divider interactions on measurements.
[Contact: Robert E. Hebner, (301) 975-2403]

Superconductors

Released for Publication

Bray, S.L., and Goodrich, L.F., **High-T_c Current Supply for DC Critical-Current Measurements.**

Precise and accurate measurements of the dc critical current of high T_c superconductors require a current supply that has high stability and low output ripple. A design for a simple and inexpensive current supply that has these characteristics is presented. The primary power source for this supply is a 12-V wet-cell battery. The typical operating range of the current supply is from 10 mA to 10 A. The performance of the supply with respect to current ripple, stability, and linearity is reported.

Superconductors (cont'd.)

[Contact: Steven L. Bray, (303) 497-5631]

Ekin, J.W., **Offset Criterion for Determining Superconductor Critical Current.**

Critical-current criteria based on electric field or resistivity can present a number of problems in defining critical current, especially for high-T_c superconductors in the vicinity of the critical temperature or upper critical field. The resulting critical-current density, J_c, can be quite arbitrary, since it depends strongly on criterion level at high fields and temperatures. These J_c definitions also create problems in distinguishing between superconductors and high-conductivity normal metals such as copper. They can also strongly bias J_c data when comparing superconductors with significantly different values of normal-state resistivity. To overcome these problems, a criterion is proposed based on the long-standing concept of a flux-flow resistivity. J_c is defined as the value on the current-density axis where an extrapolation of the tangent to the plotted curve of electric field (E) as a function of current density (J) at a point determined by a given electric-field level intersects the axis (extrapolation to zero electric field). This definition determines an offset J_c that has none of the above problems and, in addition, is independent of any flux creep voltages that may be present, since it depends entirely on the E-J characteristic in the high-current flux-flow regime. The offset J_c is shown to correspond physically to the average critical current of the critical-current distribution in the superconductor.
[Contact: Jack W. Ekin, (303) 497-5448]

Ekin, J.W., **Stress Effect**, to appear as Chapter IV-2-4 in the Handbook of Metallic Compounds.

The effects of stress on the critical current of practical high-field superconducting materials are described, including critical-current degradation from both axial and transverse strain. Possible origins of the effect are discussed. Practical engineering guidelines for application of these data to magnet design are given.
[Contact: Jack W. Ekin, (303) 497-5448]

Ekin, J.W., **VAMAS Round Robin Results of Critical Current vs. Strain in Nb_3Sn**, to be published in the Proceedings of the 6th Japan/United States Workshop on High Field Superconductors, Boulder, Colorado, February 22-24, 1989.

A comparison is made of measurements of the effect of axial tensile strain on the critical current of multifilamentary Nb_3Sn superconductors by three different laboratories. Two of the laboratories used short-sample testing apparatus wherein a straight section of conductor was cooled in a force-free state. One of the laboratories utilized a spring apparatus wherein a long sample was reacted in a coil shape and attached to a spring sample holder. The agreement between the results for the two laboratories utilizing the straight-sample apparatus was quite good, within 15% for all three conductors at 15 T, except at very high strain for one conductor which had an upper critical field close to the measurement field. To make a comparison with the data obtained using the spring method, it was necessary to fit the data to the compressive prestrain determined using the straight-sample technique. Making such a fit, the agreement was found to be variable, between 15 and 25% depending on the conductor. Values of the prestrain and irreversible strain obtained from the straight-sample data agreed within 0.06% and 0.05%, respectively. Values of the maximum (strain-free) upper critical fields agreed within several tenths of a tesla.
[Contact: Jack W. Ekin, (303) 497-5448]

Superconductors (cont'd.)

Ekin, J.W., Bray, S.L., Danielson, P., Smathers, D., Sabatini, R.L., and Suenaga, M., **Transverse Stress Effect on the Critical Current of Internal Tin and Bronze Process Nb_3Sn Superconductors**, to be published in the Proceedings of the 6th Japan/United States Workshop on High Field Superconductors, Boulder, Colorado, February 22-24, 1989.

The effect of transverse stress on the critical current density J_c has been shown to be significant in bronze-process Nb_3Sn, with the onset of significant degradation occurring at about 50 MPa. In an applied field of 10 T, the magnitude of the effect is about seven times larger for transverse stress than for axial tensile stress. We have also measured the effect in an internal tin conductor with excess tin, which yields a more equiaxed Nb_3Sn grain morphology than for bronze-process Nb_3Sn, in which the grains tend to be more columnar. The effect of transverse stress on J_c was nearly identical for the two conductors, indicating that the transverse stress effect is probably not dependent on grain morphology.
[Contact: Jack W. Ekin, (303) 497-5448]

Ekin, J.W., and Larson, T.M., **Magnetic-Field Angle Dependence of the Critical Current in Y-, Bi-, and Tl-Based High-TC Superconductors**, to be published in the Proceedings of the 6th Japan/United States Workshop on High Field Superconductors, Boulder, Colorado, February 22-24, 1989.

The change in J_c with angle between applied field and current depends on the magnetic field regime. There is essentially no change at low fields, where J_c is not determined by pinning but rather by self-field effects. At intermediate fields in the plateau regime, the effect typically amounts to a 50 to 300% enhancement in J_c for the force-free case, comparable in magnitude to conventional superconductors, indicating a nearly isotropic well-connected network of percolation paths. At high fields, field angle effect becomes negligible, indicating that the percolation paths in the high-field regime become more disconnected and highly convoluted with some section of each percolation path perpendicular to the applied field independent of the angle.
[Contact: Jack W. Ekin, (303) 497-5448]

Ekin, J.W., Larson, T.M., Hermann, A.M., Sheng, Z.Z., Togano, K., and Kumakura, H., **Double Step Critical Current vs. Field Characteristic in Y-, Bi-, and Tl-Based Bulk High-T_c Superconductors.**

A double step characteristic is observed at 76 K in the plot of transport critical current as a function of magnetic field in bulk sintered Y-, Bi-, and Tl-based high-T_c superconducting materials. The low field step-like drop in the critical current commences at magnetic fields between about 0.3 and 2 mT. This is followed by a plateau region of relatively constant critical current extending from about 30 to 300 mT, and then a second drop at fields between about 0.3 and 10 T. These features occur for all three superconductor systems and are interpreted, respectively, as a weak-link regime, a remnant percolation path regime, and a flux flow regime.
[Contact: Jack W. Ekin, (303) 497-5448]

Moreland, J., Chiang, C.K., and Swartzendruber, L.J., **Break Junction Tunneling Spectroscopy of Single-Crystal Bismuth Based High Temperature Superconductors.**

We have measured the tunneling spectra of some high-temperature superconducting crystal break junctions at 4 K. The samples were thin plates of $Bi_2SrCa_2Cu_2O_8$ compound (T_c = 110 K). The tunneling spectra (conductance versus voltage) were not typical of Bardeen-

Superconductors (cont'd.)

Cooper-Schrieffer superconductor tunneling electrodes. The spectra of higher resistance break junction settings ($R > 1\ M\Omega$) show a tunneling gap on top of a linearly increasing conductance background signal. "Harmonic" dip features in the spectra of lower resistance break junction settings ($R < 1\ M\Omega$) indicated tunneling between multiple particles in the vicinity of the primary (highest resistance) contact of the junction. The dips occurred at about the same current but shifted in voltage when the resistance of the break junction was continuously adjusted to new settings.
[Contact: John Moreland, (303) 497-3641]

Moreland, J., Ginley, D.S., Venturini, E.L., and Morosin, B., **Break Junction Measurement of the Tunneling Gap of a Thallium Based High Temperature Superconductor Crystal.**

We have used the break junction method to measure the tunneling gap of a thallium-based high-temperature superconductor crystal in liquid helium at 4 K. The crystal was predominately $Tl_2CaBa_2Cu_2O_x$ and had a Meissner onset at 105 K. Tunneling data showed a symmetric gap about zero bias between two well-defined conductance peaks in the plot of conductance as a function of voltage. The gap is consistent with a Bardeen-Cooper-Schrieffer energy gap (Δ) of 30 meV, assuming a superconductor-insulator-superconductor electrode configuration. In addition, a supercurrent could be detected when the break junction was operated in a point-contact mode at temperatures as high as 95 K.
[Contact: John Moreland, (303) 497-3641]

Nikolo, M., **Texture and Density Dependence of Grain Coupling in Sintered Y-Ba-Cu-O Superconductors.**

The ac susceptibility of sintered $Y_1Ba_2Cu_3O_{7-\delta}$ pellets was measured as a function of grain orientation at the surface (texture) and pellet density. The susceptibility measurement as a function of temperature distinguishes between shielding properties of the intrinsic superconducting grains and the weakly superconducting intergranular component. Intergrain coupling is improved when grains are aligned with their c-axes perpendicular to the sample surface such that shielding currents flow in the grains' a-b planes. This improved coupling raises the critical temperature of the intergranular component. For nontextured samples prepared at different densities, grain coupling improves with increasing pellet density, up to a characteristic density. This is attributed to increased contact area between the grains, resulting in higher critical current for the intergranular component. The ability to support larger shielding currents raises the critical temperature of the intergranular component.
[Contact: Martin Nikolo, (303) 497-5350]

Recently Published

Moreland, J., Li, Y., Folsom, R., and Capobianco, T.E., **Cryogenic Bathysphere for Rapid Variable-Temperature Characterization of High-T_c Superconductors**, Rev. Sci. Instrum., Vol. 59, No. 12, pp. 2535-2538 (December 1988).

A bathysphere consisting of an inverted dewar flask for submersible operation in cryogenic fluids is used to measure the resistance of superconductors, including high-T_c superconducting copper oxides, as a function of temperature from 4 to 300 K. We describe the cryostat incorporating the bathysphere and present data on NbTi (44% Ti) and $YBa_2Cu_3O_{7-\delta}$ with respective superconducting transition temperatures of 9.5 and 91.5 K. There are several advantages of the bathysphere method. The cryostat is of simple, compact design easily adapted to high-field applications where magnet bore size is a

Superconductors (cont'd.)

limiting factor. The sample and thermometer are thermolyzed in the dry vapor trapped at the top of the bathysphere. Temperature can be varied rapidly from 300 to 4 K at a rate of 1 K per minute with less than a 0.1-K thermal lag between the sample and thermometer.
[Contact: John Moreland, (303) 497-3641]

Moreland, J., Li, Y., Folsom, R.M., and Capobianco, T.E., **Resistance Measurements of High T_c Superconductors Using a Novel "Bathysphere" Cryostat** [original title: Novel "Bathysphere" Cryostat for Resistance Versus Temperature Experiments on High-T_c Superconductors], IEEE Transactions on Magnetics, Vol. 25, No. 2, pp. 2560-2562 (2 March 1989).

We have developed a novel cryostat for variable temperature testing of high-temperature superconductors. The cryostat is a bathysphere consisting of an overturned stainless-steel Dewar flask suspended in liquid helium. A sample-heater-thermometer assembly is located at the top of the encapsulated (and thermally insulated) vapor space inside of the Dewar. The sample can be rapidly cycled from 300 K to 4 K at an average rate of 1 K/min with a thermal hysteresis of less than 0.1 K. Helium vapor flows through a plug in the bottom of the bathysphere so that pressure of the vapor is roughly ambient. This provides ample heat transfer to and from the sample to maintain thermal equilibrium in the vapor space. Results for resistance-versus-temperature of some high-temperature superconductors in a magnetic field are presented. Also, various definitions for thermodynamic and practical critical temperatures derived from transport resistivity measurements are suggested and discussed.
[Contact: John Moreland, (303) 497-3641]

Moreland, J., Ono, R.H., Beall, J.A., Madden, M., and Nelson, A.J., **Evidence for the Superconducting Proximity Effect in Junctions Between the Surfaces of $YBa_2Cu_3O_x$ Thin Films** [original title: Superconducting Proximity Contacts Between the Surfaces of $YBa_2Cu_3O_x$ Thin Films], Appl. Phys. Lett., Vol. 54, No. 15, pp. 1477-1479 (10 April 1989).

We use the squeezable electron tunneling (SET) junction technique for testing the superconducting properties of the surfaces of $YBa_2Cu_3O_x$ (YBCO) thin-film electrodes. The I-V characteristics of the SET junctions indicate that superconductor/normal metal/superconductor contacts exist between the surfaces of the electrodes when they are allowed to touch each other. As deposited and annealed, the surfaces of the electrodes are not superconducting at 4 K. Several methods are used to improve the superconducting properties of the surfaces of the electrodes, including rapid thermal annealing, oxygen sputter etching, and thin-silver coating treatments. The greatest improvement occurs after deposition of a 5-nm Ag coating and subsequent rapid thermal anneal of the YBCO film. Under these conditions, it is possible to make a superconducting Josephson point contact between the surfaces of the electrodes. We believe that the Ag acts as a normal-metal proximity layer effectively bridging the degraded surfaces of the electrodes.
[Contact: John Moreland, (303) 497-3641]

Nikolo, M., and Goldfarb, R.B., **Flux Creep and Activation Energies at the Grain Boundaries of Y-Ba-Cu-O Superconductors**, Physical Review B, Vol. 39, No. 10, pp. 6615-6618 (1 April 1989).

We measured the ac susceptibility of sintered $Y_1Ba_2Cu_3O_{7-\delta}$ pellets as a function of temperature, applied magnetic field, and frequency. The imaginary part of susceptibility exhibits a peak below the critical

Superconductors (cont'd.)

temperature that is attributed to hysteresis losses at the grain boundaries. There is a small shift in this coupling peak towards higher temperature with frequency increasing from 10 to 1000 Hz. We explain the shift in the context of Anderson flux creep on a scale of milliseconds at the grain boundaries. The shift is dependent on the amplitude of the measuring field. The activation energy for flux creep ranges from 11.9 eV at 0.8 $A \cdot m^{-1}$ (0.01 Oe) to 1.2 eV at 800 $A \cdot m^{-1}$ (10 Oe). We extrapolate our data to find the value for an intergrain decoupling field of 1.1 $kA \cdot m^{-1}$ (14 Oe) above which the flux creep presumably becomes flux flow. We also measured a frequency shift of the intrinsic peak of the imaginary part of susceptibility, attributed to grains, for a measuring field of 4.8 $kA \cdot m^{-1}$ (60 Oe). For lower fields, there was no observed shift in the intrinsic peak as a function of frequency.
[Contact: Martin Nikolo, (303) 497-5869]

Magnetic Materials and Measurements

Released for Publication

Peterson, R.L., **Magnetization of Anisotropic Superconducting Grains.**

A critical-state calculation of the magnetization of hard type-II superconducting grains having anisotropic critical current densities is given. The grains are assumed to present rectangular cross sections to an applied magnetic field. The analysis shows how the critical-current densities should be inferred from magnetization measurements for various grain dimensions. For grains in the form of platelets, the hysteresis changes with grain size. However, for very elongated grains with anisotropic critical currents, such as may be found in the high-temperature superconductors, the magnetic hysteresis is insensitive to the lengths of the grains, and hence to powdering.
[Contact: Robert L. Peterson, (303) 497-3750]

Other Electrical Systems Topics

Recently Published

Olthoff, J.K., and Hebner, R.E., **Assessment of Space Power Related Measurement Requirements of the Strategic Defense Initiative**, NIST Technical Note 1259 (April 1989).

A survey has been performed to determine the measurement requirements of space power systems for anticipated Strategic Defense Initiative (SDI) deployments. These requirements have been compared to present state-of-the-art metrology capabilities as represented by the calibration capabilities of the National Institute of Standards and Technology. Metrology areas where present state-of-the-art capabilities are inadequate to meet SDI requirements are discussed, and areas of metrology-related research which appear promising to meet these needs are examined. Particular attention is paid to the difficulties of long-term, unattended sensor calibrations and long-term reliability of measuring systems.
[Contact: James K. Olthoff, (301) 975-2431]

ELECTROMAGNETIC INTERFERENCE

Conducted Electromagnetic Interference

Recently Published

Martzloff, F.D., **Discussion by F.D. Martzloff of IEEE PES Paper 88 SM 541-5, T.L., "Steep-Front Short-Duration Voltage Surge Tests of Power Line Filters and Transient Voltage Suppressors," by P.R. Barnes and T.L. Hudson,** IEEE Transactions on Power Delivery, Vol. 4, No. 2, pp. 1029-1036 (April 1989).

The authors report interesting results of their tests on commercial filters

Conducted EMI (cont'd.)

(presumably consisting of linear elements), enhanced by two types of nonlinear surge-protective devices. While there is no problem with the reported performance per se, the wording of the report summary suggests an inconsistency in reporting otherwise accurate results.
[Contact: Francois D. Martzloff, (301) 975-2409]

ADDITIONAL INFORMATION

Lists of Publications

Reidy, A.M., and Gibson, K.A., **A Bibliography of the NIST Electromagnetic Fields Division Publications**, NISTIR 88-3900 (September 1988).

This bibliography lists publications by the staff of the National Institute of Standards and Technology's Electromagnetic Fields Division for the period from January 1970 through August 1988. Selected earlier publications from the Division's predecessor organizations are included.
[Contact: Kathryn A. Gibson, (303) 497-3132]

DeWeese, M.E., **Metrology for Electromagnetic Technology: A Bibliography of NBS Publications**, NBSIR 88-3097 (August 1988).

This bibliography lists the publications of the personnel of the Electromagnetic Technology Division of NIST in the period from January 1970 through publication of this report. A few earlier references that are directly related to the present work of the Division are included.
[Contact: Sarabeth Moynihan, (303) 497-3678]

Palla, J.C., and Meiselman, B., **Electrical and Electronic Metrology: A Bibliography of NBS Electrosystems Division Publications, NBS List of Publications 94** (January 1989).

This bibliography covers publications of the Electrosystems Division, Center for Electronics and Electrical Engineering, NIST, and of its predecessor sections for the period January 1968 to December 1988. A brief description of the Division's technical program is given in the introduction.
[Contact: Jenny C. Palla, (301) 975-2220]

Walters, E.J., **Semiconductor Measurement Technology, NBS List of Publications 72** [a bibliography of NBS publications concerning semiconductor measurement technology for the years 1962-1988] (March 1989).

This bibliography contains reports of work performed at the National Institute of Standards and Technology in the field of Semiconductor Measurement Technology in the period from 1962 through December 1988. An index by topic area and a list of authors are provided.
[Contact: E. Jane Walters, (301) 975-2050]

NEW CALIBRATION SERVICES OFFERED

The explosive growth of optical fiber use in the communications industry has resulted in a demand for calibration services. NIST's Boulder, Colorado, laboratory now offers **measurements of optical laser power and energy at wavelengths and power levels of interest to fiber optic producers and users.** Measurements are based on a standard reference instrument called the C-series calorimeter. An electrically calibrated pyroelectric radiometer (ECPR) is calibrated against the calorimeter and is then used to calibrate optical power meters at wavelengths of 850, 1300, and 1550 nm. To improve calibration capabilities, NIST is preparing test measurement systems for detector linearity, detector uniformity, and detector spectral responsivity. These systems should be available in 6 months. For a paper outlining NIST's optical power measurement capabilities, contact Fred McGehan, Division 360, NIST, 325

Additional Information (cont'd.)

Broadway, Boulder, Colorado 80303. For more information on calibration services, contact Thomas R. Scott, Div. 724, same address, or phone (303) 497-3651.

R&D 100 AWARD WINNER

Image-Preserving Optical Delay

Edward F. Kelley of the Electrosystems Division is the recipient of an R&D 100 Award in 1988 for generating a pioneering photographic "time machine" which, when used with a high-speed camera, permits photographing events which occurred before the camera's shutter is opened.

The system, called an image-preserving optical delay, differs from conventional photography which records an event only when the shutter is open.

This new device, an arrangement of optical components including mirrors and a crystal shutter, allows researchers to take detailed, high-speed photographs of random, that is, nontriggered, events.

It is now used for processes which last from 100 ns to 10 μs to study materials utilized by the electric power industry.

This system stores optical images of a random event long enough so the shutter of a high-speed camera can be opened and photographs taken of the processes leading to the random event. Kelley has filed a patent application on the system.

Functionally, the optical delay is equivalent to forcing the image to travel an additional 120 m before it gets to the camera. Using a series of concave and planar mirrors, this path length is folded into about 4 m.

The system is rugged enough to be used in a variety of settings. Normal vibration, air currents, and airborne dust have minimal effect on its operation.
[Contact: William E. Anderson, (301) 975-2423]

RECENTLY ISSUED
STANDARD REFERENCE MATERIALS

The Semiconductor Electronics Division announces the release of a new Standard Reference Material (SRM) for **ellipsometrically derived thickness and refractive index of a silicon dioxide film on silicon**. Available for sale to the public through the NIST Office of Standard Reference Materials [for orders, (301) 975-6776], SRM 2530 is separately available for three oxide thicknesses: 50 nm (2530-1), 100 nm (2530-2), and 200 nm (2530-3).

This SRM was developed to respond to industry needs to evaluate the accuracy of ellipsometers, but may also be used as aid in the calibration of various other optical and mechanical thickness monitoring instruments.

Each SRM consists of a 76-mm (3-in.) diameter silicon wafer on which a uniform silicon dioxide layer was grown, patterned, and partially covered with chromium. The certified values were determined from measurements made using the highly accurate ellipsometer developed in the Division and are the ellipsometric parameters delta, Δ, and psi, ψ, at a wavelength of $\lambda = 632.8$ nm. The SRMs are also certified for the derived values of thickness and refractive index of its silicon dioxide layer determined by using a two-layer model consisting of a silicon dioxide layer on a thin silicon-rich oxide interlayer.
[Contact: Deane Chandler-Horowitz, (301) 975-2084]

1989/1990 CEEE CALENDAR

December 10-11, 1989 (Gaithersburg, MD)

Power Semiconductor Devices Workshop. This Workshop, sponsored jointly by IEEE

CEEE Calendar (cont'd.)

and NIST, is intended to bring together for interactive participation those actively working in the field of power semiconductor devices. It will be held in conjunction with the 1989 IEEE International Electron Devices Meeting in Washington, DC. Four specific topic areas have been selected: power and high voltage integrated circuits, discrete devices, device and circuit simulation, and packaging. In addition, a special panel on power electronics education will be held. This year's Workshop will specifically solicit attendance from device and circuit users as well as device researchers. Attendees are expected to be prepared to contribute to the development of responses to specific questions that arise in the context of the particular topic areas; a final schedule should be available at the end of October.
[Contact: David L. Blackburn, (301) 975-2068]

February 6-8, 1990 (Phoenix, AZ)

IEEE Semiconductor Thermal and Temperature Measurements Symposium. This sixth annual SEMI-THERM symposium is sponsored by the Components, Hybrids, and Manufacturing Technology Society of IEEE in cooperation with NIST and constitutes an international forum for the presentation of new developments relating to generation and removal of heat within semiconductor devices, measurement of device temperatures, and the simulation of device and system thermal behavior. Major SEMI-THERM topic areas include thermal measurements; thermal characterization; applications; and simulation, computation, and software.

The program includes keynote speakers, technical presentations, tutorial sessions, workshops, and an exhibit. In addition, the Semiconductor Equipment and Materials Institute (SEMI) and the Joint Electron Devices Engineering Council (JEDEC) have scheduled in conjunction with SEMI-THERM several Standards Committee Task Force meetings, to which attendees are invited.
[Contact: David L. Blackburn, (301) 975-2068]

September 10-12, 1990 (Boston, MA)

VLSI and GaAs Chip Packaging Workshop. The IEEE CHMT Society and the National Institute of Standards and Technology are co-sponsoring the Ninth VLSI packaging Workshop. Topics to be discussed include VLSI package design; multichip module design; WSI packaging; package thermal design; package electrical design; GaAs IC packaging; VLSI package interconnection options; VLSI package materials and die-attach solutions; and failure mechanism and quality of VLSI packages. All attendees are expected to be specialists working in the field and to participate in discussions.
[Contact: George G. Harman, (301) 975-2097]

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11. ABSTRACT (A 200-WORD OR LESS FACTUAL SUMMARY OF MOST SIGNIFICANT INFORMATION. IF DOCUMENT INCLUDES A SIGNIFICANT BIBLIOGRAPHY OR LITERATURE SURVEY, MENTION IT HERE.)

This is the twenty-seventh issue of a quarterly publication providing information on the technical work of the National Institute of Standards and Technology (formerly the National Bureau of Standards) Center for Electronics and Electrical Engineering. This issue of the CEEE Technical Progress Bulletin covers the second quarter of calendar year 1989. Abstracts are provided by technical area for both published papers and papers approved by NIST for publication.

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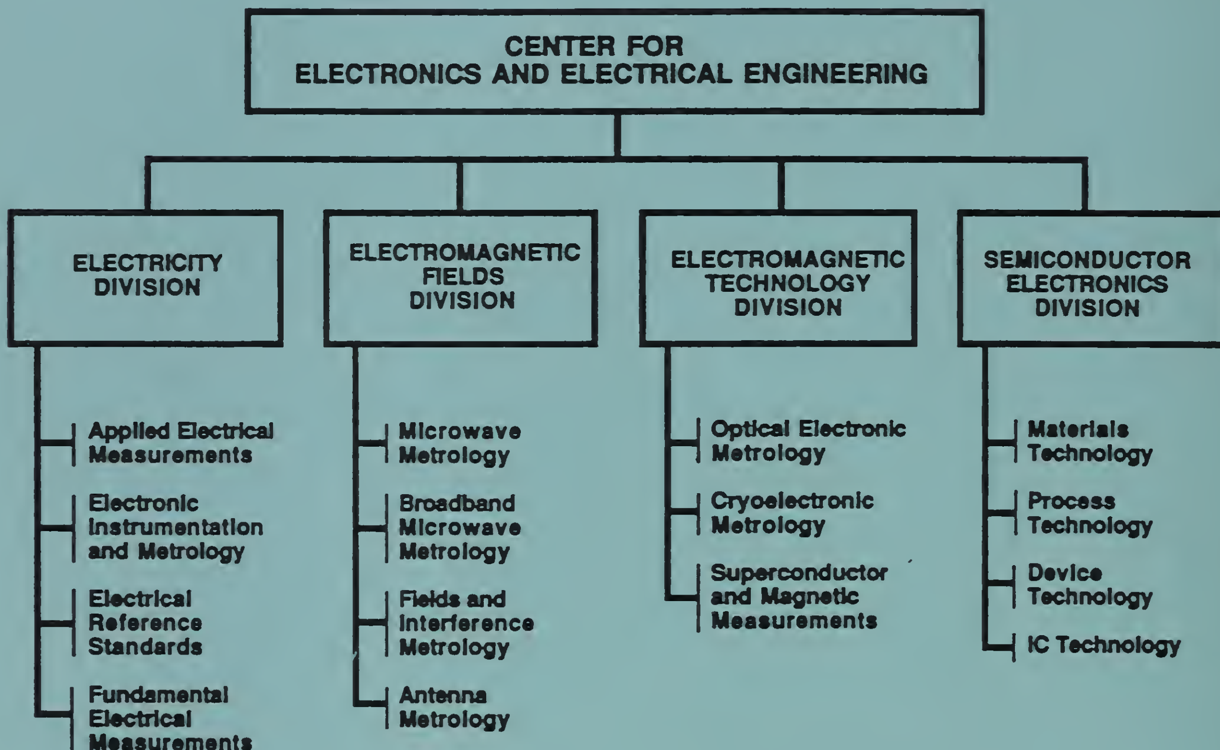

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